

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX157FT, TC74VCX157FK

Low Voltage Quad 2-Channel Multiplexer with 3.6 V Tolerant Inputs and Outputs

The TC74VCX157 is a high performance CMOS multiplexer which is guaranteed to operate from 1.2-V to 3.6-V. Designed for use in 1.5 V, 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

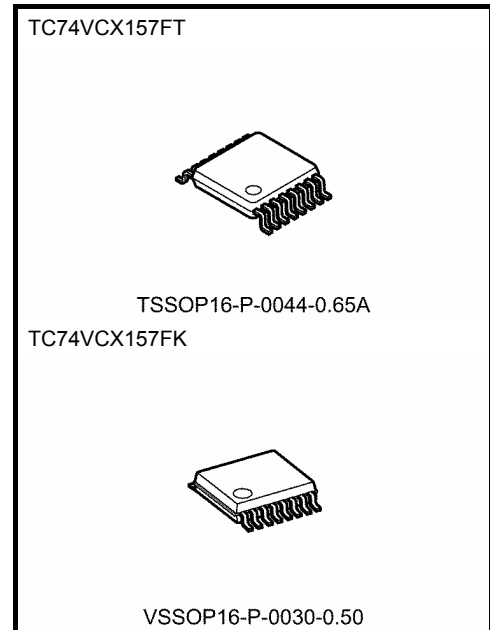
It consists of four 2-input digital multiplexers with common select and strobe inputs.

When the \overline{ST} input is held "H" level, selection of data is inhibited and all the outputs become "L" level. The SELECT decoding determines whether the A or B inputs get routed to their corresponding Y outputs.

All inputs are equipped with protection circuits against static discharge.

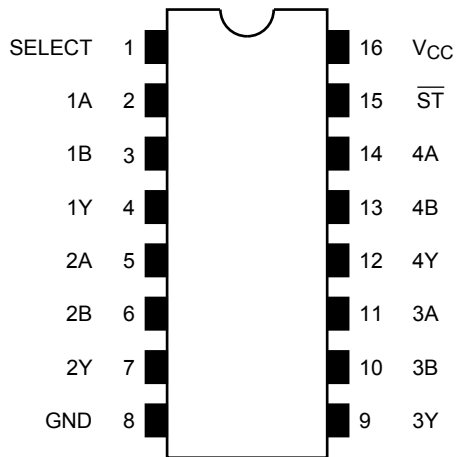
Features

- Low voltage operation: $V_{CC} = 1.2\sim 3.6\text{ V}$
- High speed operation: $t_{pd} = 3.0\text{ ns (max)} (V_{CC} = 3.0\sim 3.6\text{ V})$
 $t_{pd} = 3.5\text{ ns (max)} (V_{CC} = 2.3\sim 2.7\text{ V})$
 $t_{pd} = 7.0\text{ ns (max)} (V_{CC} = 1.65\sim 1.95\text{ V})$
 $t_{pd} = 14.0\text{ ns (max)} (V_{CC} = 1.4\sim 1.6\text{ V})$
 $t_{pd} = 35.0\text{ ns (max)} (V_{CC} = 1.2\text{ V})$
- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 24\text{ mA (min)} (V_{CC} = 3.0\text{ V})$
 $I_{OH}/I_{OL} = \pm 18\text{ mA (min)} (V_{CC} = 2.3\text{ V})$
 $I_{OH}/I_{OL} = \pm 6\text{ mA (min)} (V_{CC} = 1.65\text{ V})$
 $I_{OH}/I_{OL} = \pm 2\text{ mA (min)} (V_{CC} = 1.4\text{ V})$
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200\text{ V}$
Human body model $\geq \pm 2000\text{ V}$
- Package: TSSOP and VSSOP (US)
- Power down protection is provided on all inputs and outputs.

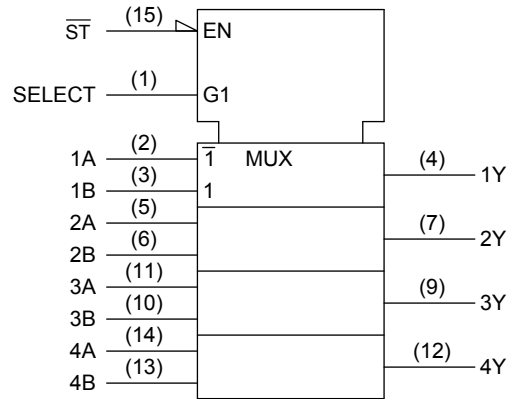


Weight	
TSSOP16-P-0044-0.65A	: 0.06 g (typ.)
VSSOP16-P-0030-0.50	: 0.02 g (typ.)

Pin Assignment (top view)



IEC Logic Symbol

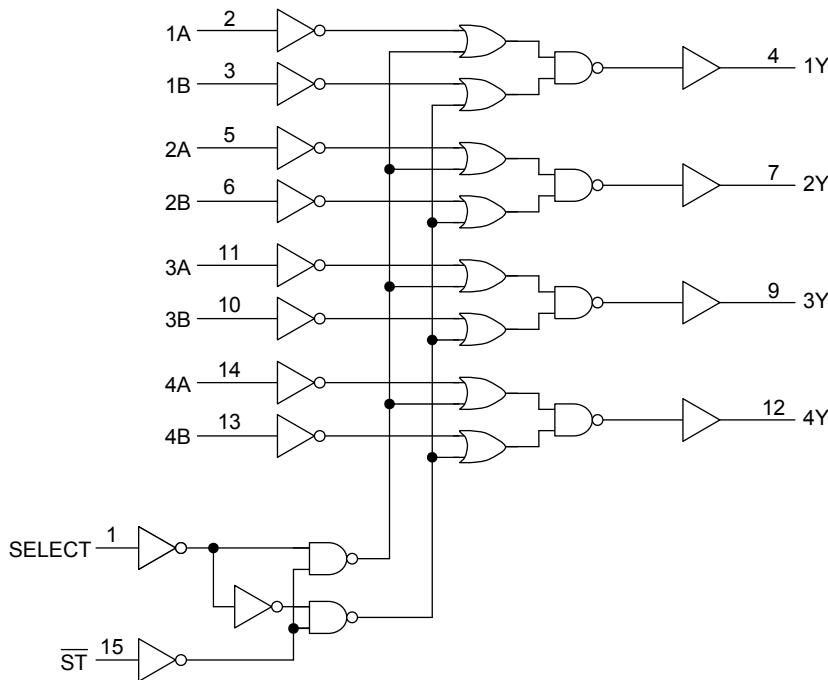


Truth Table

Inputs				Outputs
ST-bar	SELECT	A	B	Y
H	X	X	X	L
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

X: Don't care

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	-0.5~4.6	V
DC input voltage	V_{IN}	-0.5~4.6	V
DC output voltage	V_{OUT}	-0.5~4.6 (Note 2)	V
		-0.5~ $V_{CC} + 0.5$ (Note 3)	
Input diode current	I_{IK}	-50	mA
Output diode current	I_{OK}	± 50 (Note 4)	mA
DC output current	I_{OUT}	± 50	mA
Power dissipation	P_D	180	mW
DC V_{CC} /ground current	I_{CC}/I_{GND}	± 100	mA
Storage temperature	T_{stg}	-65~150	$^{\circ}C$

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: $V_{CC} = 0\text{ V}$

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	1.2~3.6	V
Input voltage	V_{IN}	-0.3~3.6	V
Output voltage	V_{OUT}	0~3.6 (Note 2)	V
		0~ V_{CC} (Note 3)	
Output current	I_{OH}/I_{OL}	± 24 (Note 4)	mA
		± 18 (Note 5)	
		± 6 (Note 6)	
		± 2 (Note 7)	
Operating temperature	T_{opr}	-40~85	$^{\circ}\text{C}$
Input rise and fall time	dt/dv	0~10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.
Unused inputs must be tied to either V_{CC} or GND.

Note 2: $V_{CC} = 0\text{ V}$

Note 3: High or low state

Note 4: $V_{CC} = 3.0\sim 3.6\text{ V}$

Note 5: $V_{CC} = 2.3\sim 2.7\text{ V}$

Note 6: $V_{CC} = 1.65\sim 1.95\text{ V}$

Note 7: $V_{CC} = 1.4\sim 1.6\text{ V}$

Note 8: $V_{IN} = 0.8\sim 2.0\text{ V}$, $V_{CC} = 3.0\text{ V}$

Electrical Characteristics

DC Characteristics ($T_a = -40\sim 85^{\circ}\text{C}$, $2.7\text{ V} < V_{CC} \leq 3.6\text{ V}$)

Characteristics		Symbol	Test Condition	$V_{CC}(\text{V})$	Min	Max	Unit	
Input voltage	High level	V_{IH}	—	2.7~3.6	2.0	—	V	
	Low level	V_{IL}	—	2.7~3.6	—	0.8		
Output voltage	High level	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -100\ \mu\text{A}$	2.7~3.6	$V_{CC} - 0.2$	—	V
				$I_{OH} = -12\ \text{mA}$	2.7	2.2	—	
				$I_{OH} = -18\ \text{mA}$	3.0	2.4	—	
				$I_{OH} = -24\ \text{mA}$	3.0	2.2	—	
	Low level	V_{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 100\ \mu\text{A}$	2.7~3.6	—	0.2	
				$I_{OL} = 12\ \text{mA}$	2.7	—	0.4	
				$I_{OL} = 18\ \text{mA}$	3.0	—	0.4	
				$I_{OL} = 24\ \text{mA}$	3.0	—	0.55	
Input leakage current		I_{IN}	$V_{IN} = 0\sim 3.6\text{ V}$	2.7~3.6	—	± 5.0	μA	
Power off leakage current		I_{OFF}	$V_{IN}, V_{OUT} = 0\sim 3.6\text{ V}$	0	—	10.0	μA	
Quiescent supply current		I_{CC}	$V_{IN} = V_{CC} \text{ or } \text{GND}$	2.7~3.6	—	20.0	μA	
			$V_{CC} \leq V_{IN} \leq 3.6\text{ V}$	2.7~3.6	—	± 20.0		
Increase in I_{CC} per input		ΔI_{CC}	$V_{IH} = V_{CC} - 0.6\text{ V}$	2.7~3.6	—	750		

DC Characteristics (Ta = -40~85°C, 2.3 V ≤ VCC ≤ 2.7 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		2.3~2.7	1.6	—	V
	Low level	V _{IL}	—		2.3~2.7	—	0.7	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	2.3	2.0	—	
				I _{OH} = -12 mA	2.3	1.8	—	
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3~2.7	—	0.2	
				I _{OL} = 12 mA	2.3	—	0.4	
				I _{OL} = 18 mA	2.3	—	0.6	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	—	±5.0	μA
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.3~2.7	—	20.0	μA
			V _{CC} ≤ V _{IN} ≤ 3.6 V		2.3~2.7	—	±20.0	

DC Characteristics (Ta = -40~85°C, 1.65 V ≤ VCC < 2.3 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		1.65~2.3	0.65 × V _{CC}	—	V
	Low level	V _{IL}	—		1.65~2.3	—	0.2 × V _{CC}	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.65~2.3	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	1.65	1.25	—	
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.65~2.3	—	0.2	
				I _{OL} = 6 mA	1.65	—	0.3	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		1.65~2.3	—	±5.0	μA
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		1.65~2.3	—	20.0	μA
			V _{CC} ≤ V _{IN} ≤ 3.6 V		1.65~2.3	—	±20.0	

DC Characteristics (Ta = -40~85°C, 1.4 V ≤ VCC ≤ 1.65 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		1.4~1.65	0.65 × V _{CC}	—	V
	Low level	V _{IL}	—		1.4~1.65	—	0.05 × V _{CC}	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.4~1.65	V _{CC} - 0.2	—	V
				I _{OH} = -2 mA	1.4	1.05	—	
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.4~1.65	—	0.05	
				I _{OL} = 2 mA	1.4	—	0.35	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		1.4~1.65	—	±5.0	μA
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		1.4~1.65	—	20.0	μA
			V _{CC} ≤ V _{IN} ≤ 3.6 V		1.4~1.65	—	±20.0	

DC Characteristics (Ta = -40~85°C, 1.2 V ≤ VCC < 1.4 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		1.2~1.4	0.8 × V _{CC}	—	V
	Low level	V _{IL}	—		1.2~1.4	—	0.05 × V _{CC}	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.2	V _{CC} - 0.1	—	V
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.2	—	0.05	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		1.2	—	±5.0	μA
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		1.2	—	20.0	μA
			V _{CC} ≤ V _{IN} ≤ 3.6 V		1.2	—	±20.0	

AC Characteristics (Ta = -40~85°C, Input: tr = tf = 2.0 ns) (Note 1)

Characteristics	Symbol	Test Condition		VCC (V)	Min	Max	Unit
Propagation delay time (A, B-Y)	t _{pLH} t _{pHL}	Figure 1, Figure 2	C _L = 15 pF, R _L = 2 kΩ	1.2	3.0	35.0	ns
				1.5 ± 0.1	2.0	14.0	
	C _L = 30 pF, R _L = 500 Ω		1.8 ± 0.15	1.5	7.0		
			2.5 ± 0.2	0.8	3.5		
Propagation delay time (SELECT-Y)	t _{pLH} t _{pHL}	Figure 1, Figure 2	C _L = 15 pF, R _L = 2 kΩ	1.2	3.0	45.0	ns
				1.5 ± 0.1	2.0	18.0	
	C _L = 30 pF, R _L = 500 Ω		1.8 ± 0.15	1.5	9.0		
			2.5 ± 0.2	0.8	4.5		
Propagation delay time (\overline{ST} -Y)	t _{pLH} t _{pHL}	Figure 1, Figure 2	C _L = 15 pF, R _L = 2 kΩ	1.2	3.0	45.0	ns
				1.5 ± 0.1	2.0	18.0	
	C _L = 30 pF, R _L = 500 Ω		1.8 ± 0.15	1.5	9.0		
			2.5 ± 0.2	0.8	4.5		
Output to output skew	t _{osLH} t _{osHL}	(Note 2)	C _L = 15 pF, R _L = 2 kΩ	1.2	—	1.5	ns
				1.5 ± 0.1	—	1.5	
	C _L = 30 pF, R _L = 500 Ω		1.8 ± 0.15	—	0.5		
			2.5 ± 0.2	—	0.5		
				3.3 ± 0.3	0.6	3.0	

Note 1: For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Note 2: This parameter is guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics (Ta = 25°C, Input: tr = tf = 2.0 ns, CL = 30 pF)

Characteristics	Symbol	Test Condition	VCC (V)	Typ.	Unit
Quiet output maximum dynamic VOL	VOLP	VIH = 1.8 V, VIL = 0 V (Note)	1.8	0.25	V
		VIH = 2.5 V, VIL = 0 V (Note)	2.5	0.6	
		VIH = 3.3 V, VIL = 0 V (Note)	3.3	0.8	
Quiet output minimum dynamic VOL	VOLV	VIH = 1.8 V, VIL = 0 V (Note)	1.8	-0.25	V
		VIH = 2.5 V, VIL = 0 V (Note)	2.5	-0.6	
		VIH = 3.3 V, VIL = 0 V (Note)	3.3	-0.8	
Quiet output minimum dynamic VOH	VOHV	VIH = 1.8 V, VIL = 0 V (Note)	1.8	1.5	V
		VIH = 2.5 V, VIL = 0 V (Note)	2.5	1.9	
		VIH = 3.3 V, VIL = 0 V (Note)	3.3	2.2	

Note: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	VCC (V)	Typ.	Unit
Input capacitance	CIN	—	1.8, 2.5, 3.3	6	pF
Power dissipation capacitance	CPD	fIN = 10 MHz (Note)	1.8, 2.5, 3.3	20	pF

Note: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

AC Test Circuit

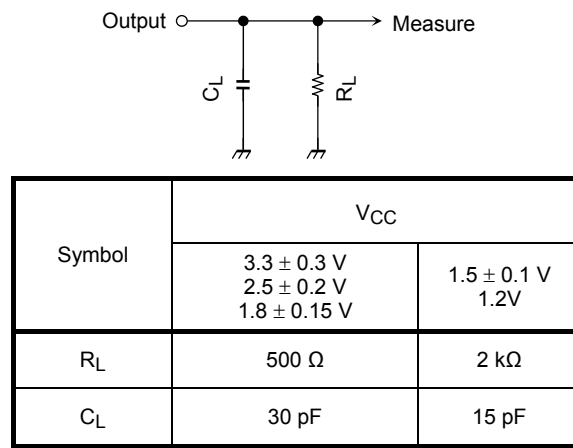
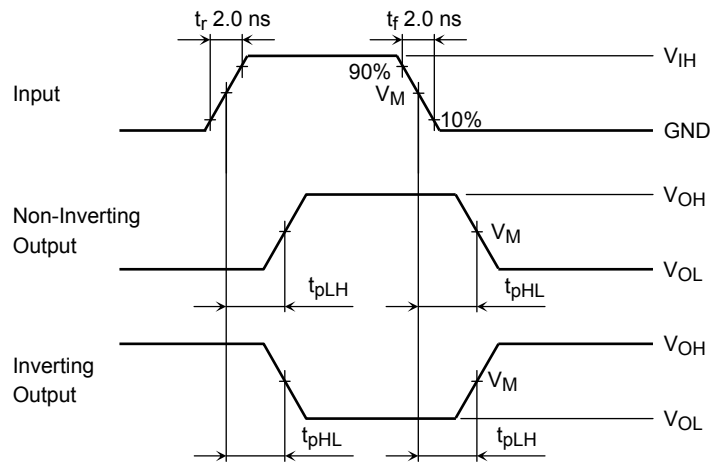


Figure 1

AC Waveform



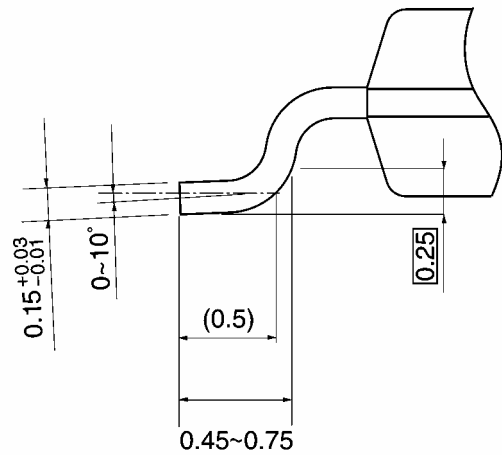
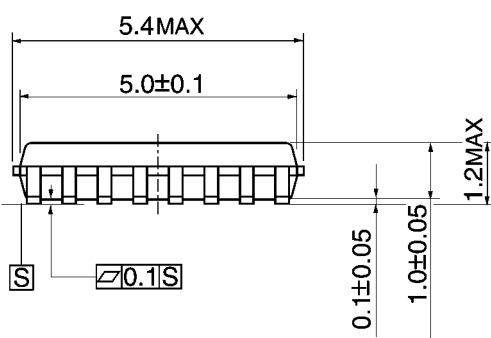
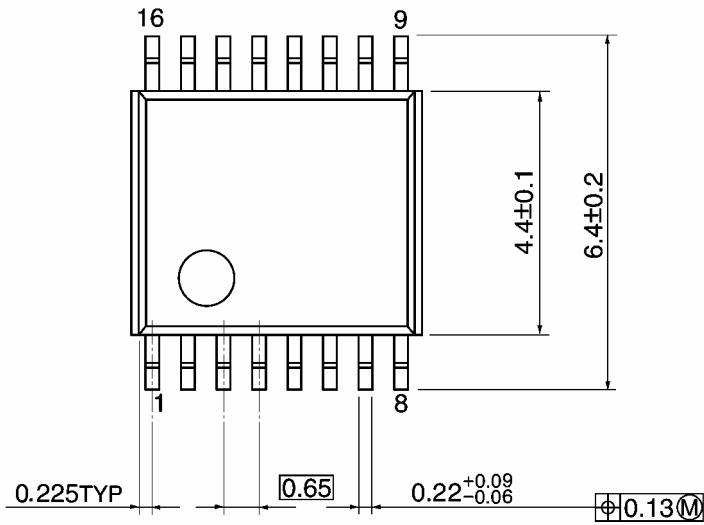
Symbol	V _{CC}				
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 ± 0.15 V	1.5 ± 0.1 V	1.2 V
V _{IH}	2.7 V	V _{CC}	V _{CC}	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2

Figure 2 t_{pLH}, t_{pHL}

Package Dimensions

TSSOP16-P-0044-0.65A

Unit: mm

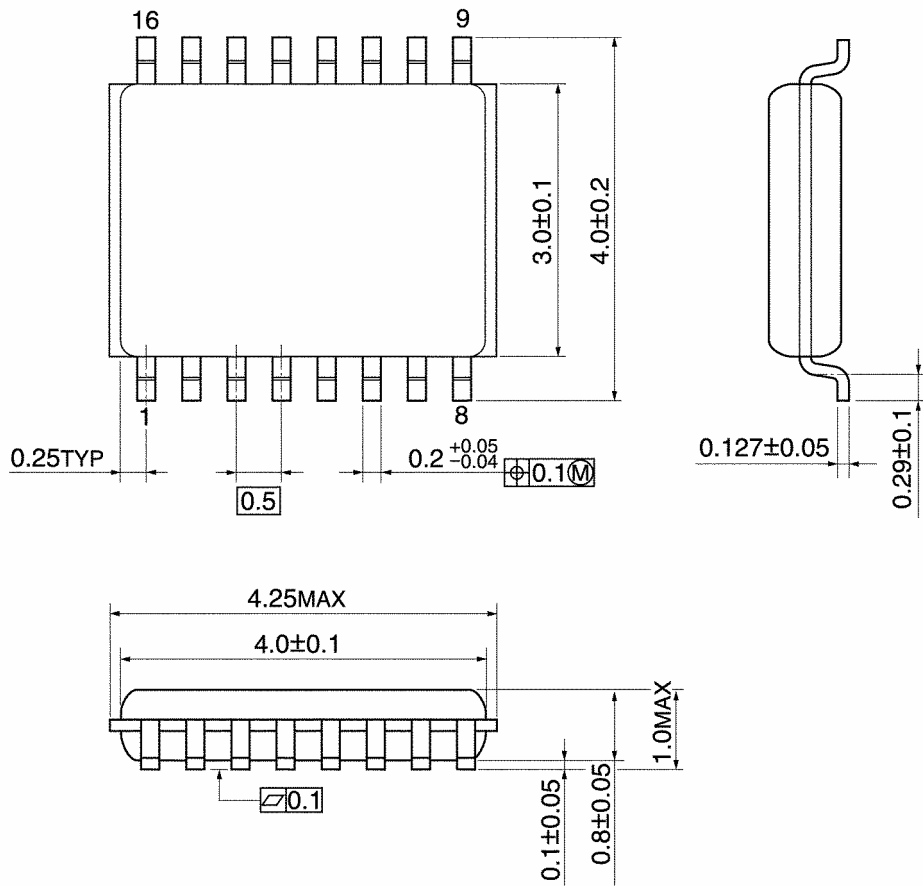


Weight: 0.06 g (typ.)

Package Dimensions

VSSOP16-P-0030-0.50

Unit: mm



Weight: 0.02 g (typ.)

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20070701-EN GENERAL

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